

<b>Form PTO-1449</b>  <b>U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>  <b>INFORMATION DISCLOSURE CITATION</b> <b>BY APPLICANT</b> (Use several sheets if necessary)	<b>Atty. Docket No.</b> 2271/66100	<b>Serial No.</b> Not Yet Assigned
<b>Applicant</b> Seiji SARAYAMA et al.		<b>Filing Date</b> Concurrently Herewith
<b>Group</b>		09/981848 10/16/01

**U.S. PATENT DOCUMENTS**

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
MAA	AA 5 8 6 8 8 3 7	February 9, 1999	DiSalvo et al.			
	AB					
	AC					
	AD					

**FOREIGN PATENT DOCUMENTS**

Document Number	Date	Country	Class	Subclass	Translation
					Yes No
MAA AL 102 5 6 6 6 2	September 25, 1998	Japan			ABST.
MAA AM 2000 327 4 9 5	November 28, 2000	Japan			ABST.
MAA AN 2000 2 2 2 1 2	January 21, 2000	Japan			ABST.
MAA AO 2000 1 2 9 0 0	January 14, 2000	Japan			ABST.

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

MAA	AP	Shuji NAKAMURA et al. "InGaN/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices", pp. L1568-L1571.
MAA	AQ	Shuji NAKAMURA et al. "InGaN/GaN/AlGaIn-Based Laser Diodes with Laser Diodes with Cleaved Facets Grown on GaN Substrates", pp. 832-834.
MAA	AR	Sylwester POROWSKI, "Bulk and Homoepitaxial GaN-growth and Characteristisation", pp. 153-158.
MAA	AS	Hisanori YAMANE et al. "Preparation of GaN Single Crystal Using a Na Flux", pp. 413-416.
MAA	AS	Appln. Serial No. 09/590,063 filed June 8, 2000

<b>EXAMINER</b> [Signature]	<b>DATE CONSIDERED</b> 7/14/03
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.